

Supporting Information

Isothermal crystallization and time-temperature-transformation diagram of the organic semiconductor 5,11-bis(triethylsilylethynyl)anthradithiophene

Liyang Yu,^{a,b*} Andrew M. Zeidell,^c John E. Anthony,^d Oana Jurchescu,^c Christian Müller^{b*}

^aSchool of Chemical Engineering, Sichuan University, Chengdu 610064, P. R. China

^bDepartment of Chemistry and Chemical Engineering, Chalmers University of Technology, 41296 Gothenburg, Sweden

^cDepartment of Physics, Wake Forest University, Winston-Salem, NC 27109, USA

^dCenter for Applied Energy Research, University of Kentucky, Lexington, KY 40511, USA

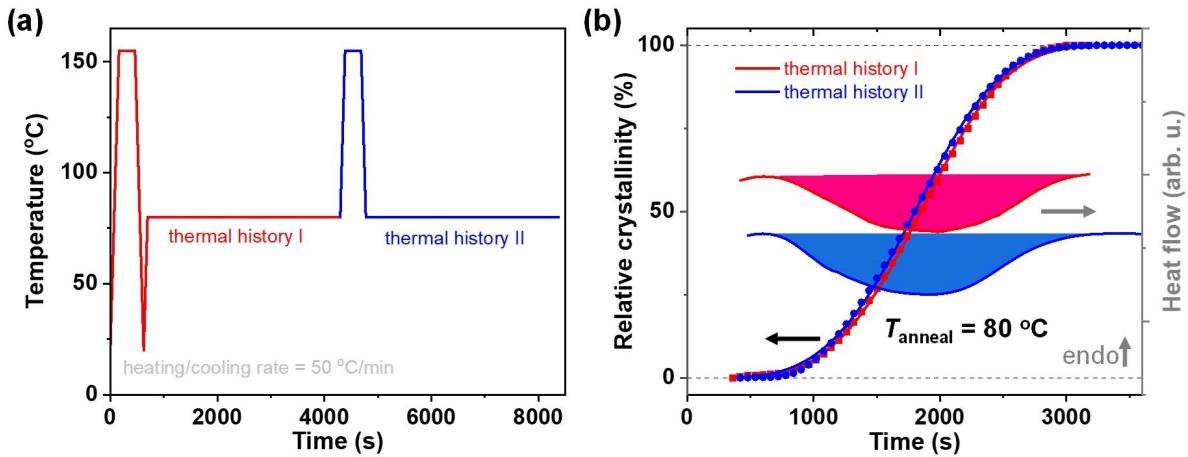


Figure S1. Comparison of the thermal history of TES-ADT quenched from 155 to 20 °C followed by heating to $T_{\text{anneal}} = 80 \text{ °C}$ (red) and from 155 °C directly to $T_{\text{anneal}} = 80 \text{ °C}$ (blue). (a) Temperature program of DSC measurements performed with a DSC 200 from Netzsch equipped with a manual liquid N₂ cooling system with heating and cooling rate of 50 °C ; and (b) isothermal DSC thermograms of TES-ADT annealed at $T_{\text{anneal}} = 80 \text{ °C}$ with different thermal histories as illustrated in (a) and the respective integrated relative crystallinity $X_c(t)$ as a function of time t (symbols) and best fits with the Avrami equation (solid lines).

Table S1. Summary of parameters describing the crystallization kinetics obtained from thermal analysis presented in Figure S1.

Thermal history	$t_{\text{onset}} \text{ (s)}$	$t_{\text{mid}} \text{ (s)}$	$t_{\text{endset}} \text{ (s)}$	$t_0 \text{ (s)}$	$\tau \text{ (s)}$	m
I	1000	1848	2646	118	1910	3.70
II	994	1799	2625	80	1901	3.69

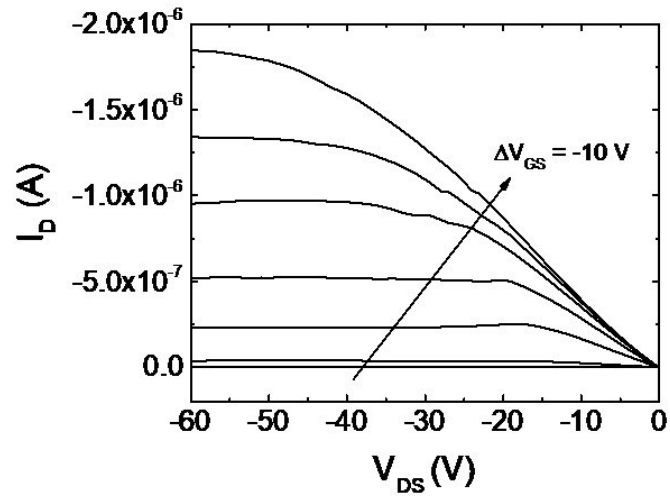


Figure S2. Output characteristics of FET device in Figure 4a.

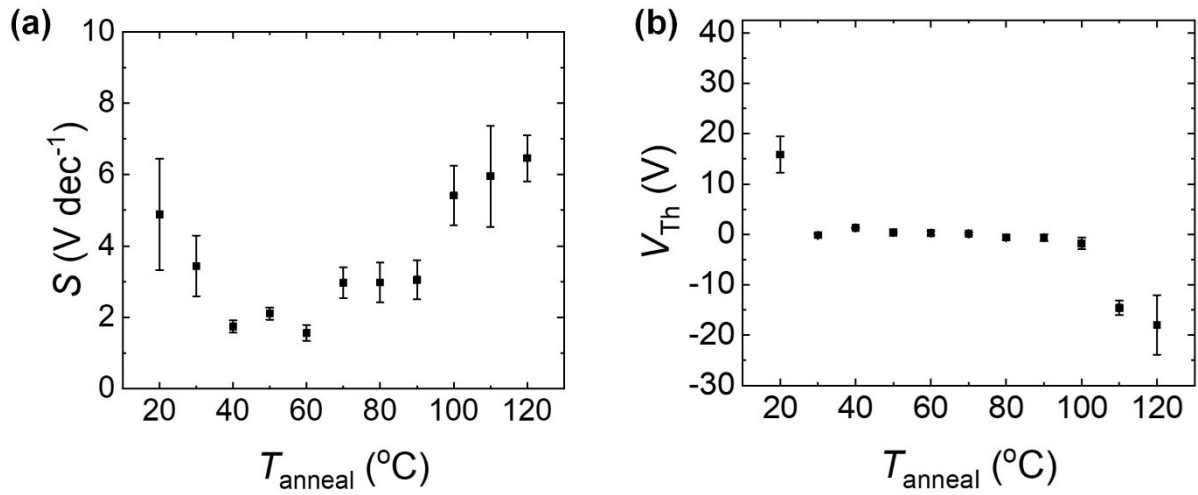


Figure S3. Plots illustrating subthreshold slope (a) and threshold voltage (b) of the FET devices against the annealing temperature.